



# FX507

NPN Epitaxial Planar Silicon Transistor

## High-Current Switching Applications

### Applications

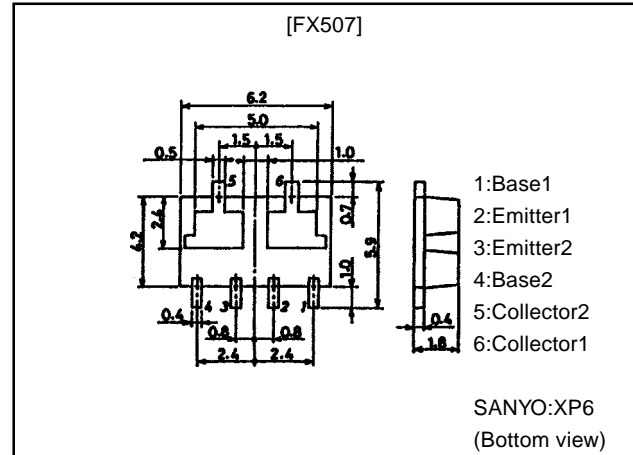
- LCD baklight drive.

### Features

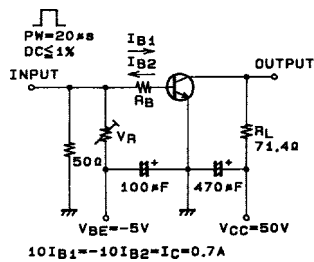
- Composite type with 2PNP transistors contained in one package, facilitating high-density mounting.
- The FX507 houses two chips, each being equivalent to the 2SC3647, in one package.
- Matched pair characteristics.

### Package Dimensions

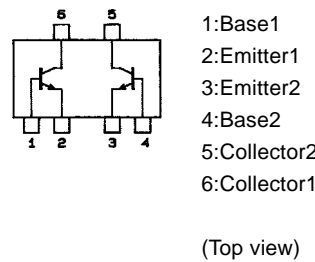
unit:mm  
2118



### Switching Time Test Circuit



### Electrical Connection



### Specifications

#### Absolute Maximum Ratings at Ta = 25°C

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	$V_{CBO}$		120	V
Collector-to-Emitter Voltage	$V_{CEO}$		100	V
Emitter-to-Base Voltage	$V_{EBO}$		6	V
Collector Current	$I_C$		2	A
Collector Current (Pulse)	$I_{CP}$		3	A
Base Current	$I_B$		400	mA
Collector Dissipation	$P_C$	Mounted on ceramic board (750mm <sup>2</sup> ×0.8mm) 1unit	1.5	W
Total Dissipation	$P_T$	Mounted on ceramic board (750mm <sup>2</sup> ×0.8mm)	2	W
Junction Temperature	$T_j$		150	°C
Storage Temperature	$T_{stg}$		-55 to +150	°C

· Marking:507

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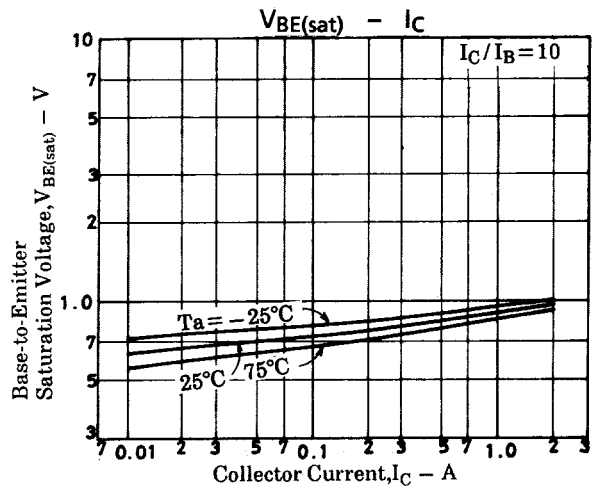
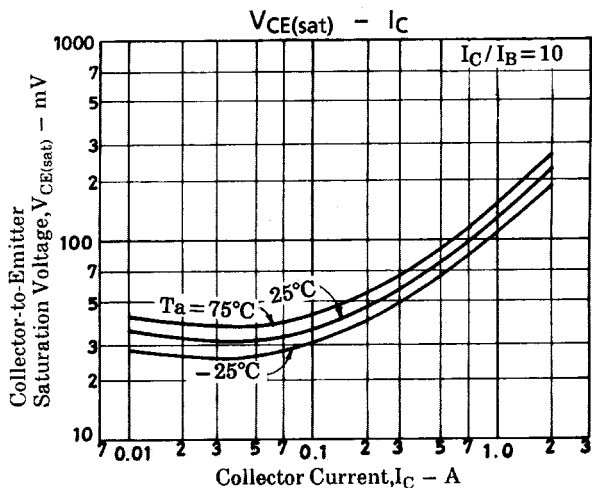
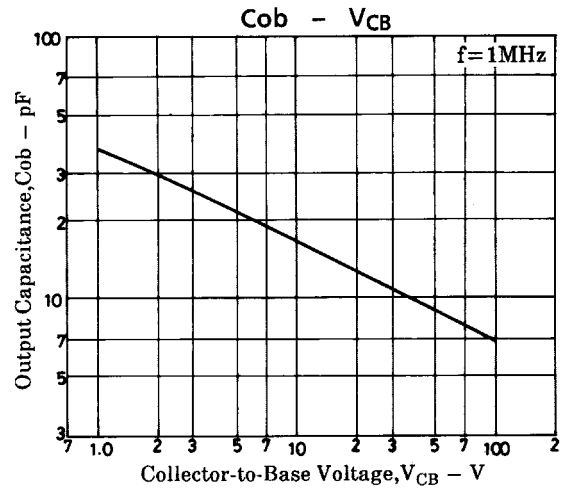
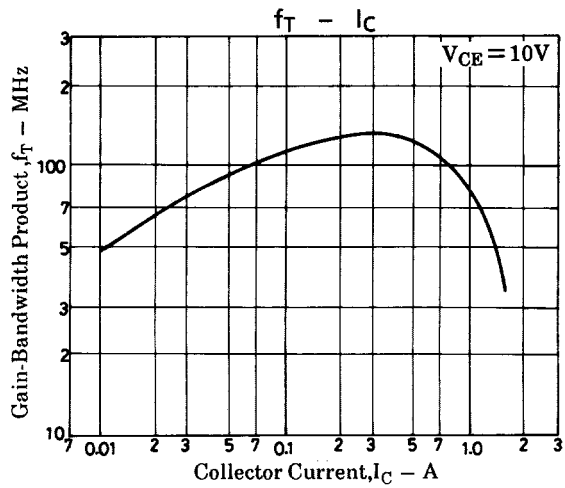
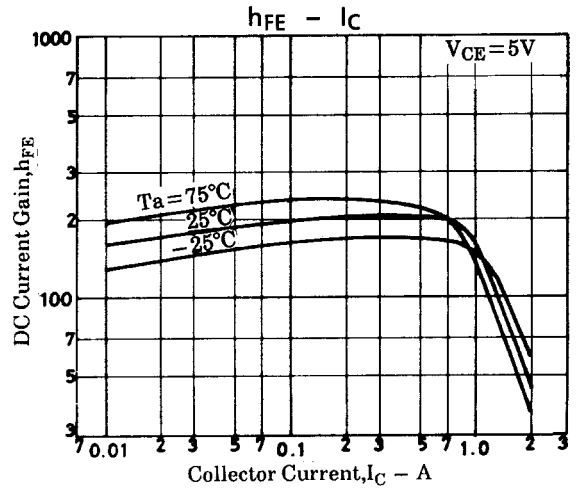
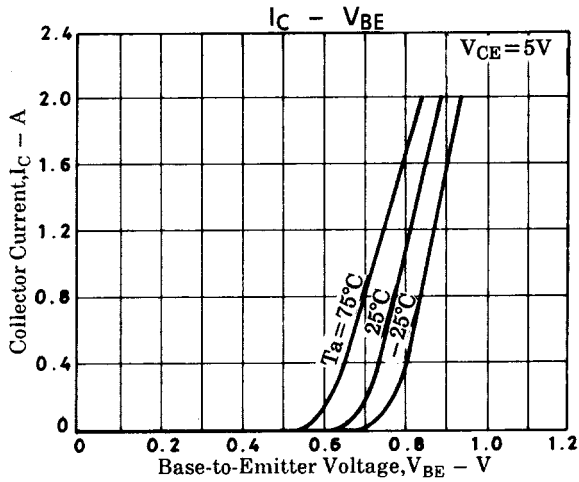
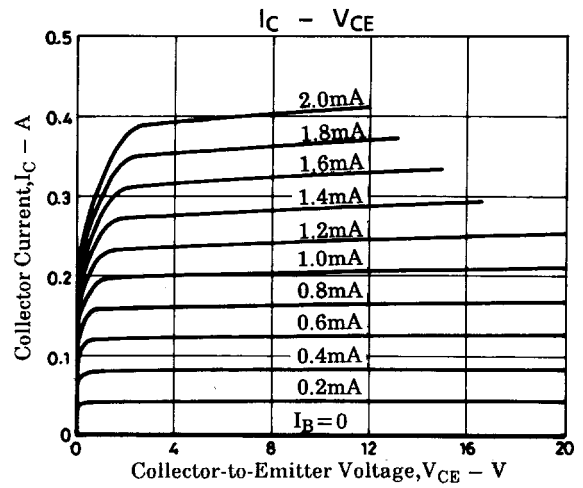
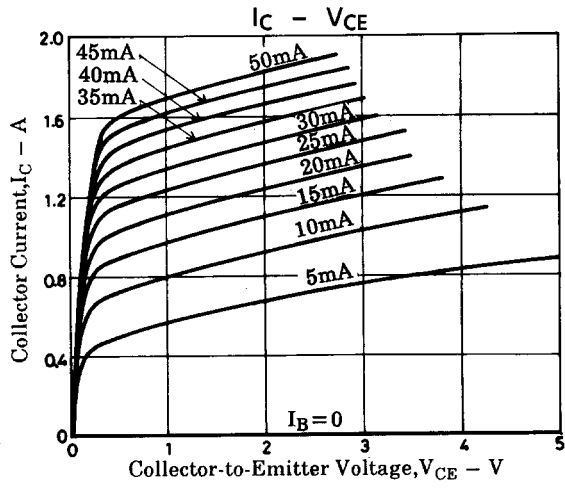
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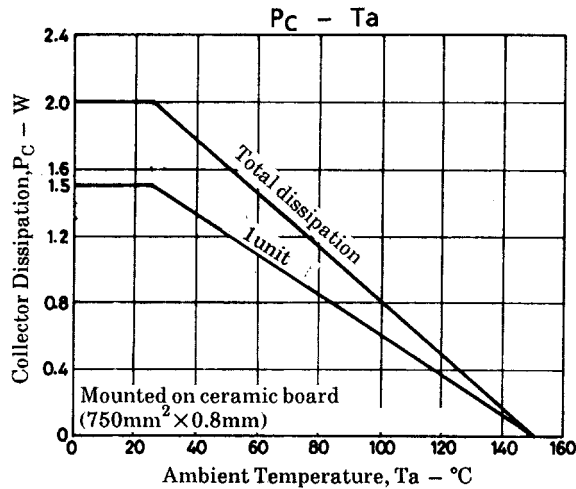
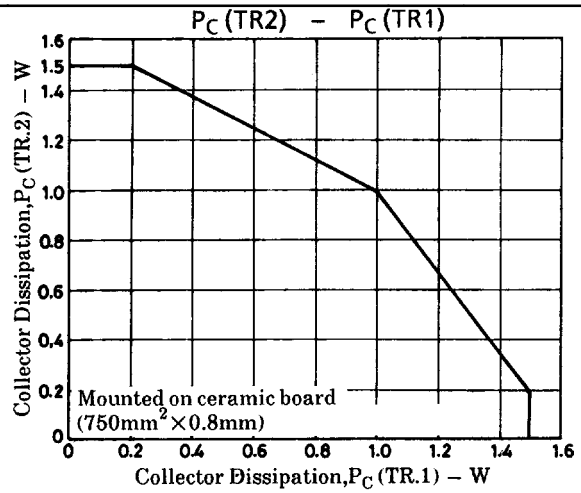
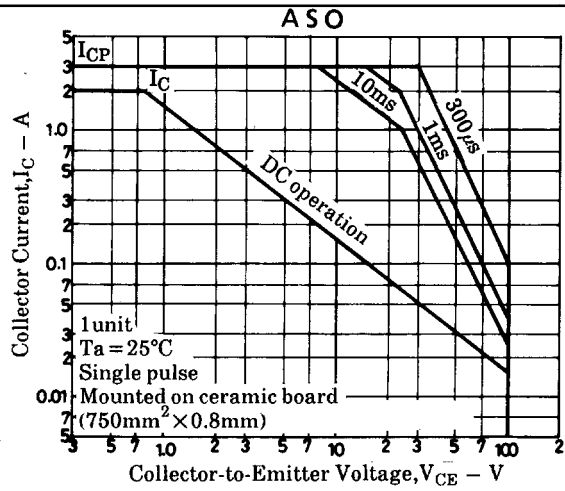
### Electrical Characteristics at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Collector Cutoff Current	$I_{CBO}$	$V_{CB}=100\text{V}, I_E=0$			100	nA
Emitter Cutoff Current	$I_{EBO}$	$V_{EB}=4\text{V}, I_C=0$			100	nA
DC Current Gain	$h_{FE}$	$V_{CE}=5\text{V}, I_C=100\text{mA}$	140		400	
DC Current Gain Ratio	$h_{FE}(\text{small/large})$	$V_{CE}=5\text{V}, I_C=100\text{mA}$	0.8			
Gain-Bandwidth Product	$f_T$	$V_{CE}=10\text{V}, I_C=100\text{mA}$		120		MHz
Output Capacitance	$C_{ob}$	$V_{CB}=10\text{V}, f=1\text{MHz}$		16		pF
C-E Saturation Voltage	$V_{CE(\text{sat})}$	$I_C=1\text{A}, I_B=100\text{mA}$		130	400	mV
B-E Saturation Voltage	$V_{BE(\text{sat})}$	$I_C=1\text{A}, I_B=100\text{mA}$		0.85	1.2	V
C-B Breakdown Voltage	$V_{(BR)CBO}$	$I_C=10\mu\text{A}, I_E=0$	120			V
C-E Breakdown Voltage	$V_{(BR)CEO}$	$I_C=1\text{mA}, R_{BE}=\infty$	100			V
E-B Breakdown Voltage	$V_{(BR)EBO}$	$I_E=10\mu\text{A}, I_C=0$	6			V
Turn-ON Time	$t_{on}$	See specified Test Circuit		80		ns
Storage Time	$t_{stg}$	See specified Test Circuit		1000		ns
Fall Time	$t_f$	See specified Test Circuit		50		ns

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